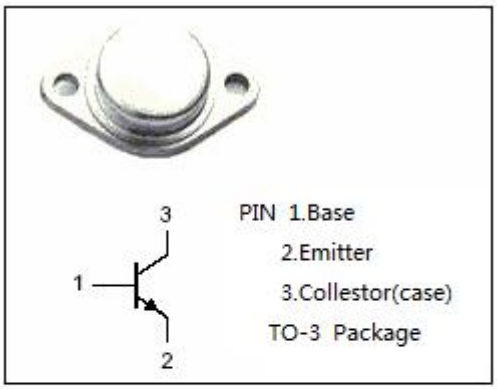
isc Silicon PNP Power Transistor 2N3790

DESCRIPTION

- Excellent Safe Operating Area
- Low Collector-Emitter Saturation Voltage
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.

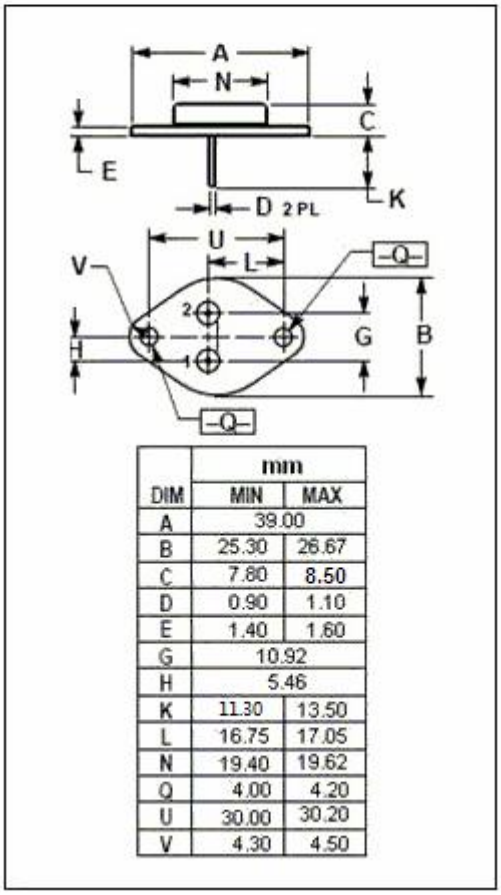


APPLICATIONS

- Designed for medium-speed switching and amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-10	A
P_C	Collector Power Dissipation@T_C=25℃	150	W
T_J	Junction Temperature	-65~200	℃
T_{stg}	Storage Temperature	-65~200	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.17	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$*	Collector-Emitter Sustaining Voltage	I_C=-200mA; I_B= 0	-80		V
I_{EBO}	Emitter Cutoff Current	V_{EB}= -7V; I_C= 0		-5	mA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -4A; I_B=- 0.4A		-1.0	V
$V_{BE(ON)-1}$	Base-Emitter On Voltage	I_C=-5A; V_{CE}=-2V		-2.0	V
$V_{BE(ON)-2}$	Base-Emitter On Voltage	I_C=-10A; V_{CE}=-4V		-4.0	V
h_{FE-1}	DC Current Gain	I_C= -1A; V_{CE}= -2V	25	90	
h_{FE-2}	DC Current Gain	I_C= -3A; V_{CE}= -2V	15		
f_T	Current Gain-Bandwidth Product	I_C= -0.5A; V_{CE}= -10V; f= 1.0MHz	4		MHz

*:Pulse test:Pulse width=300us,duty cycle≤2%